Remarks

Claims 1-19 were pending prior to the entry of the amendment above. Claims 1-19 are currently amended. New claim 20 has been added. Reconsideration is requested in light of the amendments above and below remarks.

The Examiner has objected to claims 5-8 and 10-19 as being multiple dependent claims depending upon multiple dependent claims. The multiple dependent claims have been amended, thus reconsideration is urged.

Claims 1, 2 and 4-19 were rejected as unclear. Claims 1, 2 and 16 are amended to change "1" to "I". Claims 16 and 17 no longer recite "CaN". Claims 4-19 no longer recite "device or method". Reconsideration is urged.

The Examiner has rejected independent claim 1 as obvious in light of Frijlink and Molnar (6,086,673). Reconsideration is requested in light of the amendments above.

Frijlink relates to a reactor for MOVPE of III-V semiconductors, where seven 2 inch wafers or five three inch wafers are in planetary motion in a circular growth chamber. The planetary motion is achieved by using a levitation and rotation technique applied to the substrate holder.

Molnar relates to a method for producing a nitride layer on a growth substrate. First a pretreatment layer is formed on the growth substrate, and then the formed pretreatment layer is exposed to a gaseous environment that is thermochemically reactive with the pretreatment layer. After gaseous environment exposure of the pretreatment layer, there is carried out an epitaxial growing process to produce on the substrate a nitride layer material.

Independent claim 1 requires, among other limitations, a reaction chamber having an axis of symmetry, and a multiplicity of rotationally driven substrate holders arranged annularly about the axis of symmetry on the substrate holder, the separately heatable sources being disposed adjacent to the axis of symmetry inside the reaction chamber. Neither reference either taken alone, or in combination discloses the claimed configuration. Frinjlink relates to a different type of vapor deposition where the main hydrogen carrier gas, the group III organometallics and the dopants enter the device through the inner tube 10. *See* page 208. Thus, Finjlink fails to suggest locating sources inside the reaction chamber. Similarly, Molnar does not include sources adjacent to the axis of symmetry inside the reaction chamber. Conversely, in Molnar, the synthesis and growth chambers are isolated by a boat 22 located at the bottom of the synthesis chamber for holding Ga metal for the precursor synthesis process. A precursor delivery injector is further required to deliver the precursor products. *See e.g.* Col. 5 lines, 55-67. Accordingly, neither reference taken alone or in combination show the sources located in the reaction chamber.

Moreover, Molnar teaches away from the present invention by including boat 22. The boat edges seal with the reaction tube liner 12 to isolate the chambers. Thus, the precursors are isolated from the process chamber and one of ordinary skill in the art would not be motivated to combine this reference teaching with Finjlink , which relates to another type of vapor deposition, to configure the apparatus to include separately heatable sources being disposed adjacent to the axis of symmetry inside the reaction chamber. Accordingly, amended claim 1 is not obvious.

It is respectfully submitted that claims 1-20 are in condition for allowance and early notification to that effect is requested.

Respectfully submitted,

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